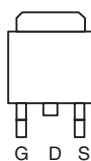


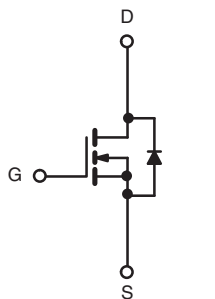
Automotive N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	150
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.019
I_D (A)	85
Configuration	Single

TO-263


Top View



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified^d
- Find out more about Vishay's Automotive Grade Product Requirements at: www.vishay.com/applications



RoHS
COMPLIANT
HALOGEN
FREE

ORDERING INFORMATION

Package	TO-263
Lead (Pb)-free and Halogen-free	SQM85N15-19-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	85	A
		50	
Continuous Source Current (Diode Conduction) ^a	I_S	120	
Pulsed Drain Current ^b	I_{DM}	140	
Single Pulse Avalanche Energy	I_{AS}	52	mJ
Single Pulse Avalanche Current	E_{AS}	135	
Maximum Power Dissipation ^b	P_D	375	W
		125	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes

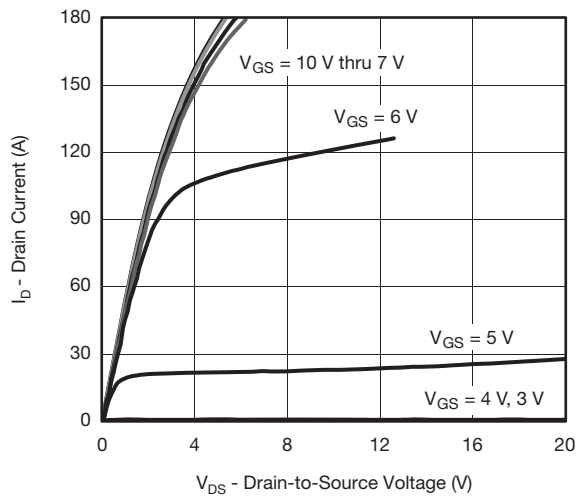
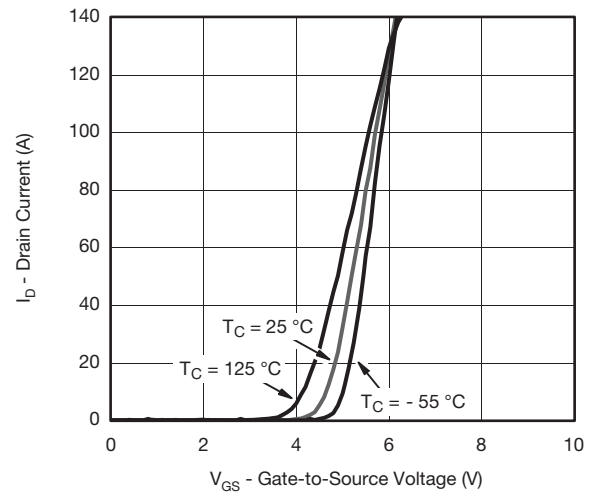
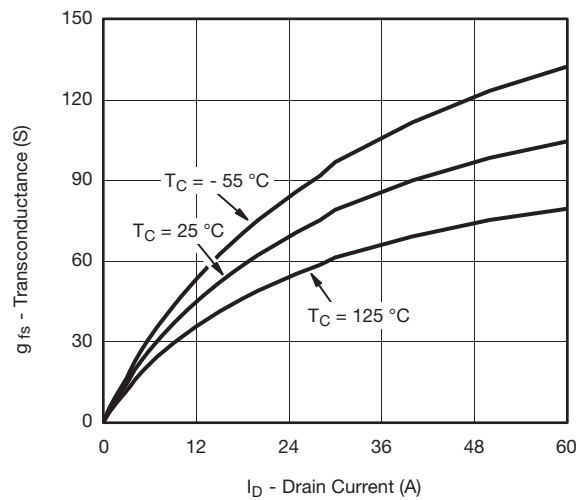
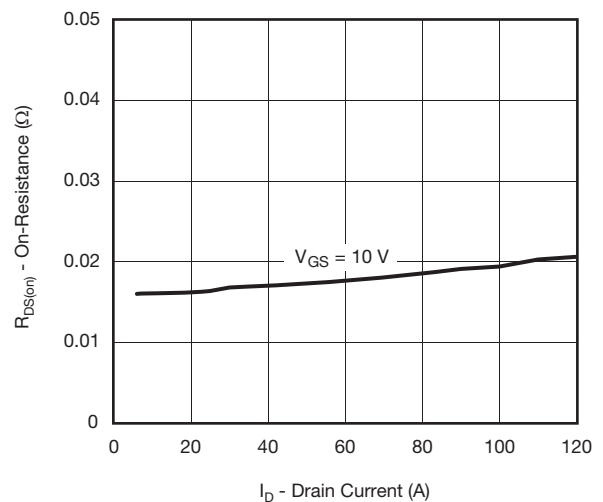
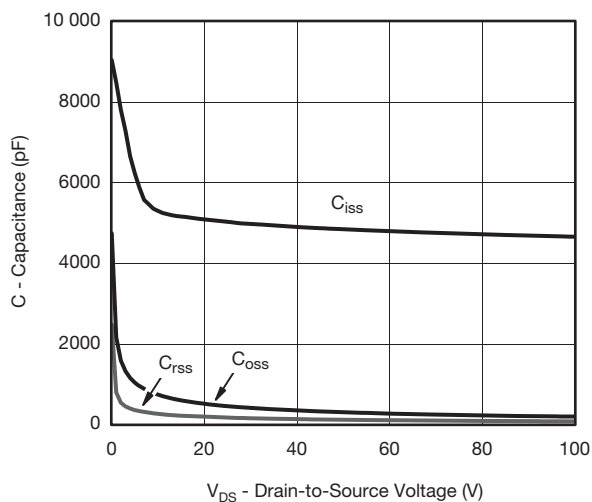
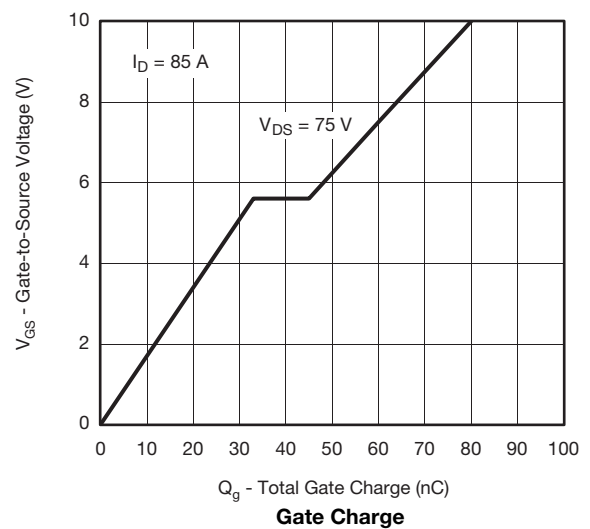
- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square P.C.B. (Fr-4 material).
- Parametric verification ongoing.

SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		150	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3.0	3.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V	-	-	1.0	μA
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 175 °C	-	-	300	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.016	0.019	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.039	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.051	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	79	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	5026	6285	pF
Output Capacitance	C _{oss}			-	450	565	
Reverse Transfer Capacitance	C _{rss}			-	165	205	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 75 V, I _D = 85 A	-	80	120	nC
Gate-Source Charge ^c	Q _{gs}			-	33	-	
Gate-Drain Charge ^c	Q _{gd}			-	12	-	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 75 V, R _L = 0.88 Ω I _D ≅ 85 A, V _{GEN} = 10 V, R _g = 1 Ω		-	17	26	ns
Rise Time ^c	t _r			-	24	36	
Turn-Off Delay Time ^c	t _{d(off)}			-	35	53	
Fall Time ^c	t _f			-	11	17	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	140	A
Forward Voltage	V _{SD}	I _F = 85 A, V _{GS} = 0 V		-	0.9	1.5	V

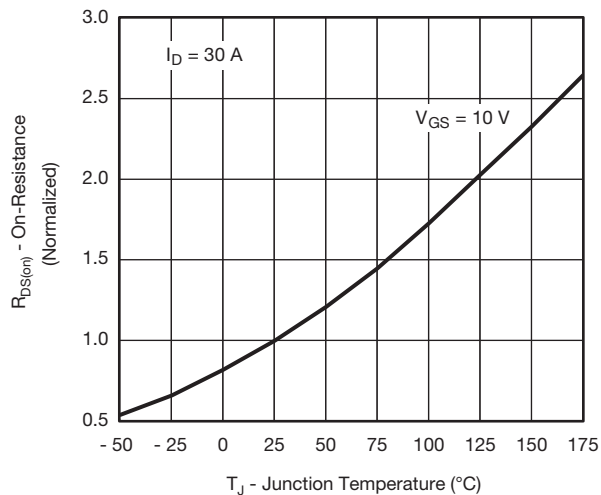
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

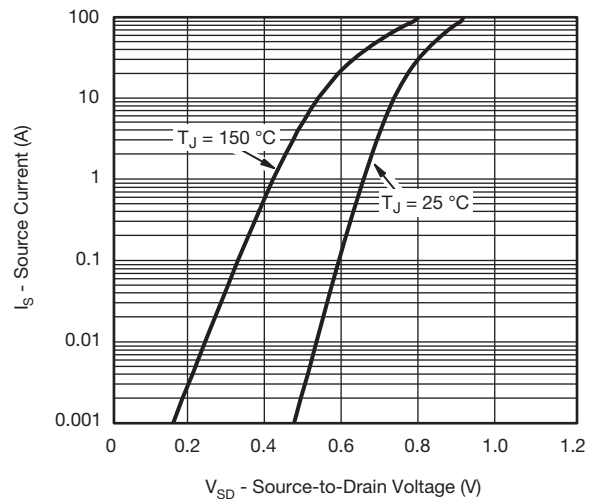
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

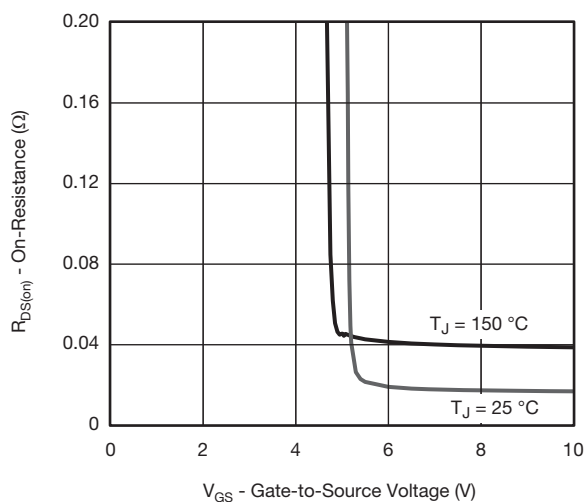
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



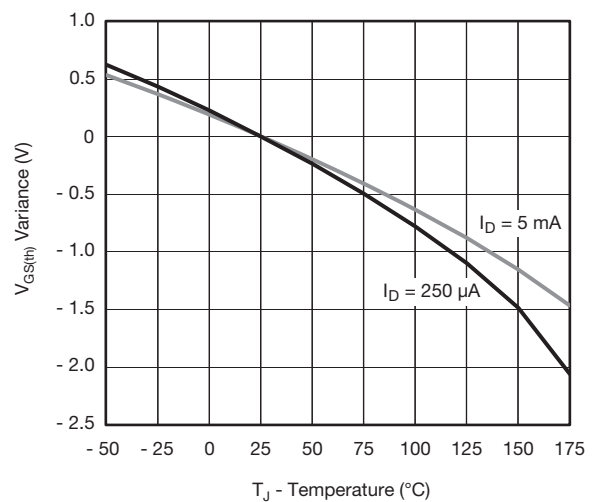
On-Resistance vs. Junction Temperature



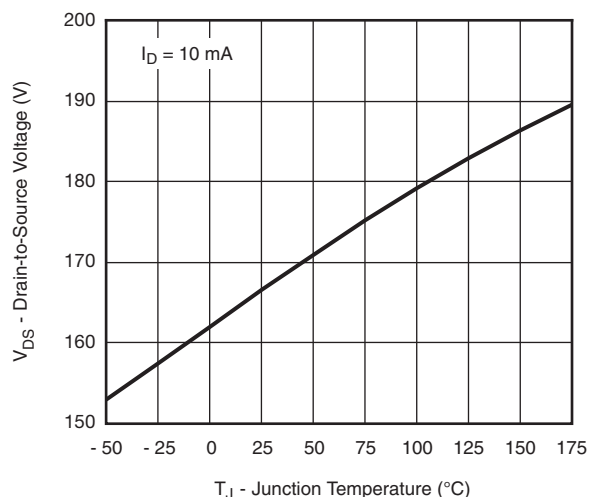
Source Drain Diode Forward Voltage



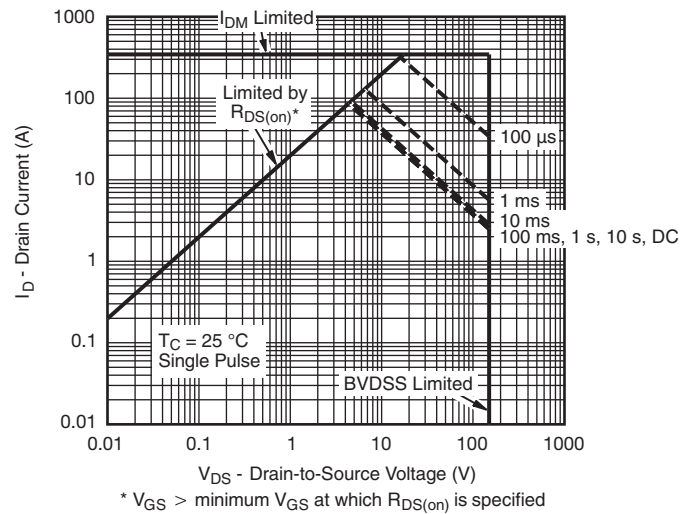
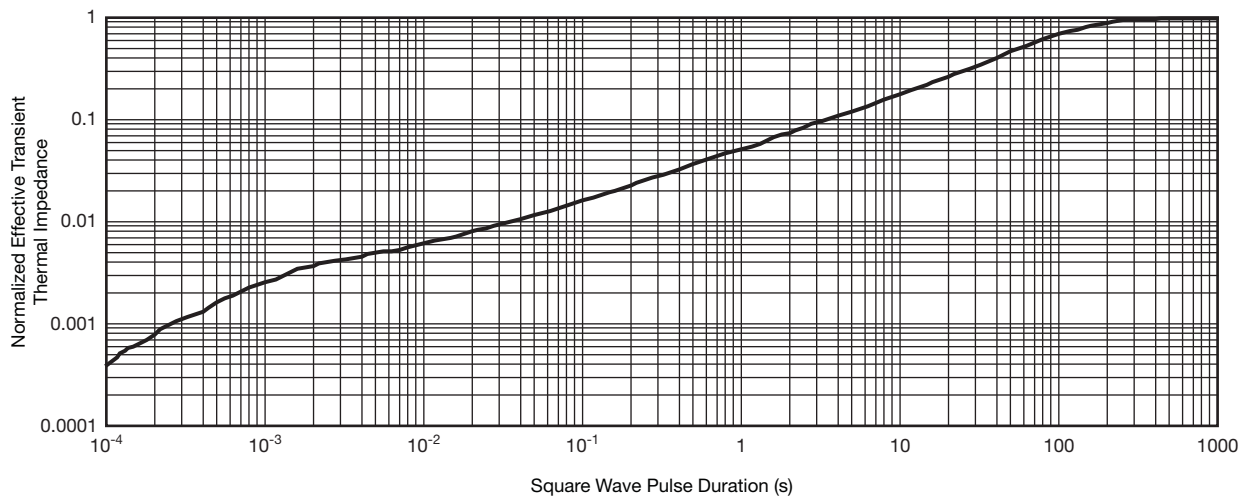
On-Resistance vs. Gate-to-Source Voltage



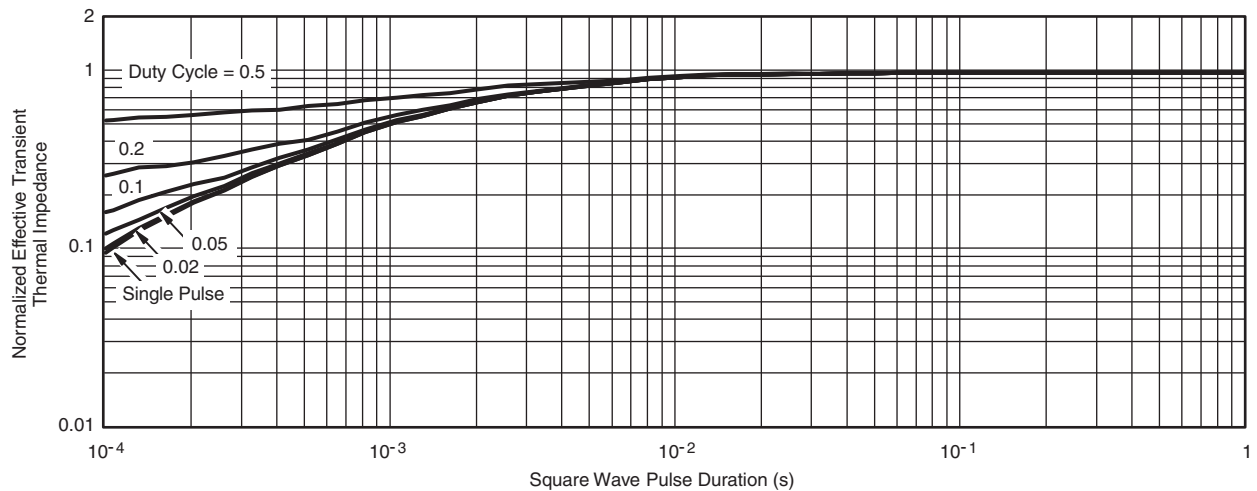
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Safe Operating Area

Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



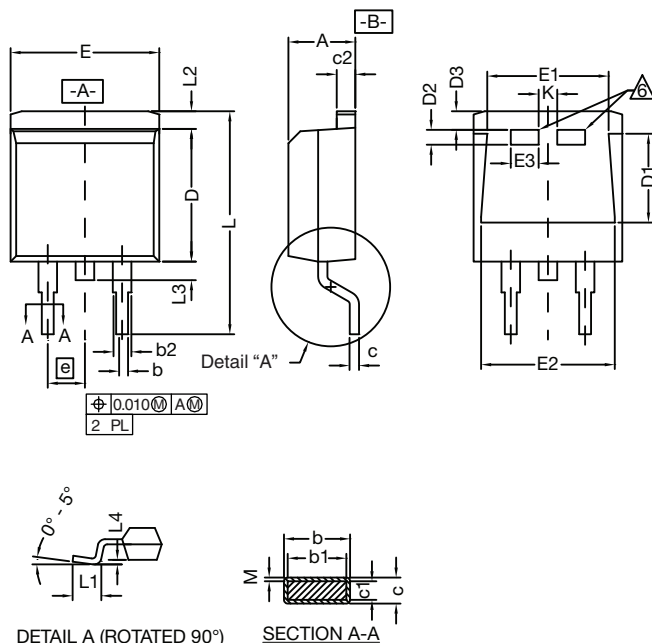
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68668.

TO-263 (D²PAK): 3-LEAD



DIM.		INCHES		MILLIMETERS	
		MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050
ECN: T10-0738-Rev. J, 03-Jan-11					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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